

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A laser irradiation apparatus comprising:
a first laser oscillator generating a first pulsed laser beam having a wavelength at which an absorption coefficient to the processing object is $1 \times 10^4 \text{ cm}^{-1}$ or more;
means for controlling a shape and a position of a beam spot of the first laser beam;
a second laser oscillator generating a second continuous wave laser beam;
means for controlling a shape and a position of a beam spot of the second laser beam to overlap with the beam spot of the first laser beam; and
means for controlling a relative position of the beam spot of the first laser beam and the beam spot of the second laser beam to the processing object.
2. (Original) A laser irradiation apparatus according to claim 1,
wherein the first laser beam has a wavelength of second harmonic.
3. (Original) A laser irradiation apparatus according to claim 1,
wherein the second laser beam has a wavelength of fundamental wave.
4. (Original) A laser irradiation apparatus according to claim 1,
wherein the beam spot of the first laser beam is elliptical, rectangular, or linear.
5. (Original) A laser irradiation apparatus according to claim 1,
wherein the beam spot of the second laser beam is elliptical, rectangular, or linear.

6. (Original) A laser irradiation apparatus according to claim 1,
wherein the first laser oscillator is selected from the group consisting of an Ar laser, a Kr laser, an excimer laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, a glass laser, a ruby laser, an alexandrite laser, a Ti: sapphire laser, a copper vapor laser, and a gold vapor laser.

7. (Original) A laser irradiation apparatus according to claim 1,
wherein the second laser oscillator is selected from the group consisting of an Ar laser, a Kr laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, an alexandrite laser, a Ti: sapphire laser, and a helium-cadmium laser.

8. (Original) A laser irradiation apparatus according to claim 1,
wherein:
the processing object comprises a substrate having a thickness of "d" which is transparent to the first laser beam; and
an incident angle " $\Phi 1$ " of the first laser beam to a surface of the processing object satisfies an inequality of $\Phi 1 \geq \arctan (W1/2d)$ when W1 is defined as a length of a major axis or a minor axis of the beam spot of the first laser beam.

9. (Original) A laser irradiation apparatus according to claim 1,
wherein:
the processing object comprises a substrate having a thickness of "d" which is transparent to the second laser beam; and
an incident angle " $\Phi 2$ " of the second laser beam to a surface of the processing object satisfies an inequality of $\Phi 2 \geq \arctan (W2/2d)$ when W2 is defined as a length of a major axis or a minor axis of the beam spot of the second laser beam.

10. (Original) A laser irradiation apparatus comprising:
a first laser oscillator generating a first pulsed laser beam having a wavelength of visible light or a shorter wavelength than that of visible light;
means for controlling a shape and a position of a beam spot of the first laser beam;
a second laser oscillator generating a second continuous wave laser beam;
means for controlling a shape and a position of a beam spot of the second laser beam to overlap with the beam spot of the first laser beam; and
means for controlling a relative position of the beam spot of the first laser beam and the beam spot of the second laser beam to a processing object.

11. (Currently Amended) A laser irradiation apparatus according to claim [[2]]
10,
wherein the first laser beam has a wavelength of second harmonic.

12. (Currently Amended) A laser irradiation apparatus according to claim [[2]]
10,
wherein the second laser beam has a wavelength of fundamental wave.

13. (Currently Amended) A laser irradiation apparatus according to claim [[2]]
10,
wherein the beam spot of the first laser beam is elliptical, rectangular, or linear.

14. (Currently Amended) A laser irradiation apparatus according to claim [[2]]
10,
wherein the beam spot of the second laser beam is elliptical, rectangular, or linear.

15. (Currently Amended) A laser irradiation apparatus according to claim [[2]]
10,

wherein the first laser oscillator is selected from the group consisting of an Ar laser, a Kr laser, an excimer laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, a glass laser, a ruby laser, an alexandrite laser, a Ti: sapphire laser, a copper vapor laser, and a gold vapor laser.

16. (Currently Amended) A laser irradiation apparatus according to claim [[2]]
10,

wherein the second laser oscillator is selected from the group consisting of an Ar laser, a Kr laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, an alexandrite laser, a Ti: sapphire laser, and a helium-cadmium laser.

17. (Currently Amended) A laser irradiation apparatus according to claim [[2]]
10,

wherein:

the processing object comprises a substrate having a thickness of "d" which is transparent to the first laser beam; and

an incident angle " $\Phi 1$ " of the first laser beam to a surface of the processing object satisfies an inequality of $\Phi 1 \geq \arctan (W1/2d)$ when W1 is defined as a length of a major axis or a minor axis of the beam spot of the first laser beam.

18. (Currently Amended) A laser irradiation apparatus according to claim [[2]]
10,

wherein:

the processing object comprises a substrate having a thickness of "d" which is transparent to the second laser beam; and

an incident angle " Φ_2 " of the second laser beam to a surface of the processing object satisfies an inequality of $\Phi_2 \geq \arctan(W_2/2d)$ when W_2 is defined as a length of a major axis or a minor axis of the beam spot of the second laser beam.

19. (Currently Amended) A laser irradiation method comprising the step ~~[[of;]]~~
of:

irradiating a processing object with a first pulsed laser beam having a wavelength at which an absorption coefficient to the processing object is $1 \times 10^4 \text{ cm}^{-1}$ or more and a second continuous wave laser beam,

wherein when the first laser beam and the second laser beam are irradiated, a beam spot formed on a surface of the processing object by the first laser beam and a beam spot formed on the surface of the processing object by the second laser beam are overlapped.

20. (Original) A laser irradiation method according to claim 19,
wherein the first laser beam has a wavelength of second harmonic.

21. (Original) A laser irradiation method according to claim 19,
wherein the second laser beam has a wavelength of fundamental wave.

22. (Original) A laser irradiation method according to claim 19,
wherein the beam spot formed on the surface of the processing object by the first laser beam is elliptical, rectangular, or linear.

23. (Original) A laser irradiation method according to claim 19,
wherein the beam spot formed on the surface of the processing object by the second laser beam is elliptical, rectangular, or linear.

24. (Original) A laser irradiation method according to claim 19,
wherein the first laser beam is emitted from a laser oscillator selected from the group consisting of an Ar laser, a Kr laser, an excimer laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, a glass laser, a ruby laser, an alexandrite laser, a Ti: sapphire laser, a copper vapor laser, and a gold vapor laser.

25. (Currently Amended) A laser irradiation method according to claim 19,
wherein the second laser beam is emitted from a laser oscillator selected from the group consisting of an Ar laser, a Kr laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, an alexandrite laser, a Ti: sapphire laser, and a helium-cadmium laser.

26. (Original) A laser irradiation method according to claim 19,
wherein:
the processing object comprises a substrate having a thickness of "d" which is transparent to the first laser beam; and
an incident angle " $\Phi 1$ " of the first laser beam to the surface of the processing object satisfies an inequality of $\Phi 1 \geq \arctan (W1/2d)$ when W1 is defined as a length of a major axis or a minor axis of the beam spot formed on the surface of the processing object by the first laser beam.

27. (Original) A laser irradiation method according to claim 19,
wherein:
the processing object comprises a substrate having a thickness of "d" which is transparent to the second laser beam; and
an incident angle " $\Phi 2$ " of the second laser beam to the surface of the processing object satisfies an inequality of $\Phi 2 \geq \arctan (W2/2d)$ when W2 is defined as a length of a

major axis or a minor axis of the beam spot formed on the surface of the processing object by the second laser beam.

28. (Currently Amended) A laser irradiation method comprising the step ~~[[of;]]~~ of:

irradiating a processing object with a first pulsed laser beam having a wavelength of visible light or a shorter wavelength than that of visible light and a second continuous wave laser beam,

wherein when the first laser beam and the second laser beam are irradiated, a beam spot formed on a surface of the processing object by the first laser beam and a beam spot formed on the surface of the processing object by the second laser beam are overlapped.

29. (Original) A laser irradiation method according to claim 28,
wherein the first laser beam has a wavelength of second harmonic.

30. (Original) A laser irradiation method according to claim 28,
wherein the second laser beam has a wavelength of fundamental wave.

31. (Original) A laser irradiation method according to claim 28,
wherein the beam spot formed on the surface of the processing object by the first laser beam is elliptical, rectangular, or linear.

32. (Original) A laser irradiation method according to claim 28,
wherein the beam spot formed on the surface of the processing object by the second laser beam is elliptical, rectangular, or linear.

33. (Original) A laser irradiation method according to claim 28,

wherein the first laser beam is emitted from a laser oscillator selected from the group consisting of an Ar laser, a Kr laser, an excimer laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, a glass laser, a ruby laser, an alexandrite laser, a Ti: sapphire laser, a copper vapor laser, and a gold vapor laser.

34. (Currently Amended) A laser irradiation method according to claim 28,

wherein the second laser beam is emitted from a laser oscillator selected from the group consisting of an Ar laser, a Kr laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, an alexandrite laser, a Ti: sapphire laser, and a helium-cadmium laser.

35. (Original) A laser irradiation method according to claim 28,

wherein:

the processing object comprises a substrate having a thickness of "d" which is transparent to the first laser beam; and

an incident angle " $\Phi 1$ " of the first laser beam to the surface of the processing object satisfies an inequality of $\Phi 1 \geq \arctan (W1/2d)$ when W1 is defined as a length of a major axis or a minor axis of the beam spot formed on the surface of the processing object by the first laser beam.

36. (Original) A laser irradiation method according to claim 28,

wherein:

the processing object comprises a substrate having a thickness of "d" which is transparent to the second laser beam; and

an incident angle " $\Phi 2$ " of the second laser beam to the surface of the processing object satisfies an inequality of $\Phi 2 \geq \arctan (W2/2d)$ when W2 is defined as a length of a

major axis or a minor axis of the beam spot formed on the surface of the processing object by the second laser beam.

37. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps ~~[[of;]]~~ of:

forming a semiconductor film on ~~[[a]]~~ an insulating surface; and

irradiating the semiconductor film with a first pulsed laser beam having a wavelength at which an absorption coefficient to the semiconductor film is $1 \times 10^4 \text{ cm}^{-1}$ or more and a second continuous wave laser beam to crystallize the semiconductor film,

wherein when the first laser beam and the second laser beam are irradiated, a beam spot formed on a surface of the semiconductor film by the first laser beam and a beam spot formed on the surface of the semiconductor film by the second laser beam are overlapped.

38. (Original) A method for manufacturing a semiconductor device according to claim 37,

wherein the first laser beam has a wavelength of second harmonic.

39. (Original) A method for manufacturing a semiconductor device according to claim 37,

wherein the first laser beam has a wavelength of the fundamental wave.

40. (Original) A method for manufacturing a semiconductor device according to claim 37,

wherein the beam spot formed on the surface of the semiconductor film by the first laser beam is elliptical, rectangular, or linear.

41. (Original) A method for manufacturing a semiconductor device according to claim 37,

wherein the beam spot formed on the surface of the semiconductor film by the second laser beam is elliptical, rectangular or linear.

42. (Original) A laser irradiation method according to claim 37,

wherein the first laser beam is emitted from a laser oscillator selected from the group consisting of an Ar laser, a Kr laser, an excimer laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, a glass laser, a ruby laser, an alexandrite laser, a Ti: sapphire laser, a copper vapor laser, and a gold vapor laser.

43. (Original) A laser irradiation method according to claim 37,

wherein the second laser beam is emitted from laser oscillator selected from the group consisting of an Ar laser, a Kr laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, an alexandrite laser, a Ti: sapphire laser, and a helium-cadmium laser.

44. (Currently Amended) A method for manufacturing a semiconductor device according to claim 37,

wherein:

the semiconductor film is formed over a substrate comprising the insulating surface and having a thickness of "d" which is transparent to the first laser beam; and

an incident angle " $\Phi 1$ " of the first laser beam to the surface of the semiconductor film satisfies an inequality of $\Phi 1 \geq \arctan (W1/2d)$ when W1 is defined as a length of a major axis or a minor axis of the beam spot formed on the surface of the semiconductor film by the first laser beam.

45. (Currently Amended) A method for manufacturing a semiconductor device according to claim 37,

wherein:

the semiconductor film is formed over a substrate comprising the insulating surface and having a thickness of "d" which is transparent to the second laser beam; and

an incident angle " $\Phi 2$ " of the second laser beam to the surface of the semiconductor film satisfies an inequality of $\Phi 2 \geq \arctan (W2/2d)$ when W2 is defined as a length of a major axis or a minor axis of the beam spot formed on the surface of the semiconductor film by the second laser beam.

46. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps ~~[[of;]]~~ of:

forming a semiconductor film on ~~[[a]]~~ an insulating surface; and

irradiating the semiconductor film with a first pulsed laser beam having a wavelength of visible light or a shorter wavelength than that of visible light and a second continuous wave laser beam to crystallize the semiconductor film,

wherein when the first laser beam and the second laser beam are irradiated, a beam spot formed on a surface of the semiconductor film by the first laser beam and a beam spot formed on the surface of the semiconductor film by the second laser beam are overlapped.

47. (Original) A method for manufacturing a semiconductor device according to claim 46,

wherein the first laser beam has a wavelength of second harmonic.

48. (Original) A method for manufacturing a semiconductor device according to claim 46,

wherein the first laser beam has a wavelength of the fundamental wave.

49. A method for manufacturing a semiconductor device according to claim 46,
wherein the beam spot formed on the surface of the semiconductor film by the first laser beam is elliptical, rectangular, or linear.

50. (Original) A method for manufacturing a semiconductor device according to claim 46,
wherein the beam spot formed on the surface of the semiconductor film by the second laser beam is elliptical, rectangular or linear.

51. (Original) A laser irradiation method according to claim 46,
wherein the first laser beam is emitted from a laser oscillator selected from the group consisting of an Ar laser, a Kr laser, an excimer laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, a glass laser, a ruby laser, an alexandrite laser, a Ti: sapphire laser, a copper vapor laser, and a gold vapor laser.

52. (Currently Amended) A laser irradiation method according to claim 46,
wherein the second laser beam is emitted from a laser oscillator selected from the group consisting of an Ar laser, a Kr laser, a CO₂ laser, a YAG laser, a Y₂O₃ laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, an alexandrite laser, a Ti: sapphire laser, and a helium-cadmium laser.

53. (Currently Amended) A method for manufacturing a semiconductor device according to claim 46,
wherein:
the semiconductor film is formed over a substrate comprising the insulating surface and having a thickness of "d" which is transparent to the first laser beam; and

an incident angle " $\Phi 1$ " of the first laser beam to the surface of the semiconductor film satisfies an inequality of $\Phi 1 \geq \arctan (W1/2d)$ when $W1$ is defined as a length of a major axis or a minor axis of the beam spot formed on the surface of the semiconductor film by the first laser beam.

54. (Currently Amended) A method for manufacturing a semiconductor device according to claim 46,

wherein:

the semiconductor film is formed over a substrate comprising the insulating surface and having a thickness of " d " which is transparent to the second laser beam; and

an incident angle " $\Phi 2$ " of the second laser beam to the surface of the semiconductor film satisfies an inequality of $\Phi 2 \geq \arctan (W2/2d)$ when $W2$ is defined as a length of a major axis or a minor axis of the beam spot formed on the surface of the semiconductor film by the second laser beam.